

ABSTRACT

5 A process for fabricating a semiconductor device, including applying an immersion lithography medium to a surface of a semiconductor wafer; exposing a material on the surface of the semiconductor wafer to electromagnetic radiation having a selected wavelength; and applying supercritical carbon dioxide to the semiconductor wafer to remove the immersion lithography medium from the surface of the semiconductor wafer. In one embodiment, the process includes recovery of the immersion lithography medium.